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N-Channel 80 V (D-S) Super Junction Power MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|-----------------------------------|--------------------|-----------------------|--|--|--|
| V _{DS} (V) | R _{DS(on)} (Ω) MAX. | I _D (A) | Q _g (TYP.) | | | |
| 80 | 0.0021 at V _{GS} = 10 V | 200 | 168 nC | | | |
| | 0.0027 at V _{GS} = 4.5 V | 180 | 100110 | | | |

TO-220 Pin Configuration

Top View N-Channel MOSFET

FEATURES

- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested

APPLICATIONS COMPLIANT

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | | | |
|---|-----------------------------------|-----------------|------------------|----|--|--|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | | | |
| Drain-Source Voltage | V_{DS} | 80 | | | | | |
| Gate-Source Voltage | V _{GS} | ± 20 | V | | | | |
| Continuous Drain Current /T = 150 °C | T _C = 25 °C | | 200 | | | | |
| Continuous Drain Current (T _J = 150 °C) | T _C = 125 °C | l _D | 140 | | | | |
| Pulsed Drain Current (t = 100 μs) | I _{DM} | 800 | Α | | | | |
| Avalanche Current L = 0.1 mH | | I _{AS} | 190 | | | | |
| Single Avalanche Energy ^a | L=0.11IIII | E _{AS} | 1925 | mJ | | | |
| Maximum Power Dissipation ^a | T _C = 25 °C | В | 300 b | W | | | |
| Maximum Fower Dissipation 4 | T _C = 125 °C | P _D | 125 ^b | | | | |
| Operating Junction and Storage Temperature R | T _J , T _{stg} | -55 to +175 | °C | | | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|-------------------|-------|------|--|--|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | | |
| Junction-to-Ambient (PCB Mount) ^c | R _{thJA} | 2.1 | °C/W | | | |
| Junction-to-Case (Drain) | R _{thJC} | 0.5 | C/VV | | | |

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|--|----------------------|--|------|--------|--------|------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 80 | - | - | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 1 | - | 3 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA | |
| | | V _{DS} = 80 V, V _{GS} = 0 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C | - | - | 100 | μΑ | |
| | | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$ | - | - | 2 | mA | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$ | 200 | - | - | Α | |
| Drain Source On State Besistance | D- | | | 0.0021 | 0.0027 | - | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$ | - | 0.0028 | 0.0036 | Ω | |
| Forward Transconductance ^a g_{fs} $V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$ | | V _{DS} = 15 V, I _D = 30 A | - | 90 | - | S | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | - | 10500 | - | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$ | - | 1650 | - | | |
| Reverse Transfer Capacitance | C _{rss} | | - | 75 | - | | |
| Total Gate Charge ^c | Q_g | | - | 168 | | nC | |
| Gate-Source Charge ^c | Q_{gs} | $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$ | - | 55 | - | | |
| Gate-Drain Charge ^c | Q_{gd} | | - | 23 | - | | |
| Gate Resistance | R_g | f = 1 MHz | | 2.3 | | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | - | 28 | - | ns | |
| Rise Time ^c | t _r | $V_{DD} = 50 \text{ V}, \text{ R}_{L} = 1.67 \Omega$ | - | 75 | - | | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | - | 88 | - | | |
| Fall Time ^c | t _f | | - | 32 | - | | |
| Drain-Source Body Diode Ratings and | nd Characteri | stics ^b (T _C = 25 °C) | | | | | |
| Pulsed Current (t = 100 μs) | I _{SM} | | - | - | 800 | Α | |
| Forward Voltage ^a | V _{SD} | I _F = 30 A, V _{GS} = 0 V | - | 0.7 | 1.2 | V | |
| Reverse Recovery Time | t _{rr} | | - | 118 | - | ns | |
| Peak Reverse Recovery Charge | I _{RM(REC)} | $I_F = 30 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$ | - | 5 | 10 | Α | |
| Reverse Recovery Charge | Q_{rr} | | - | 305 | - | μC | |

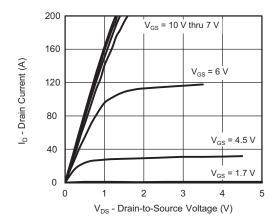
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

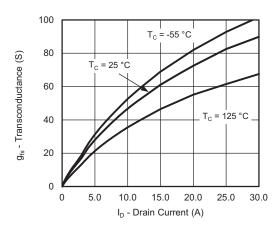
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



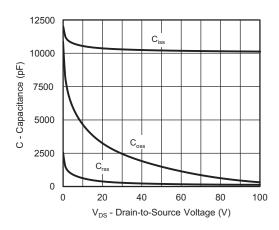
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



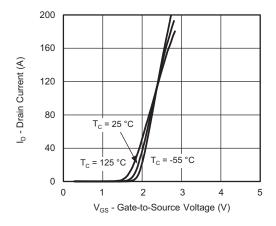
Output Characteristics



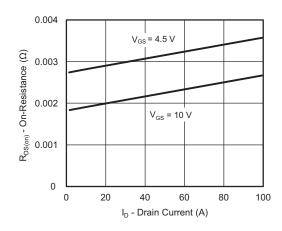
Transconductance



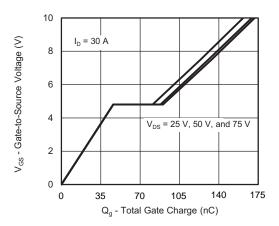
Capacitance



Transfer Characteristics



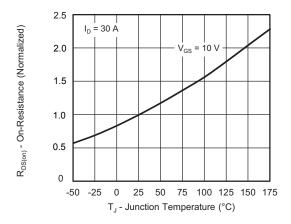
On-Resistance vs. Drain Current



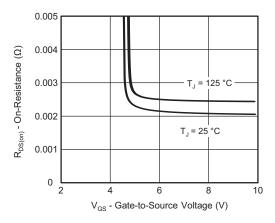
Gate Charge



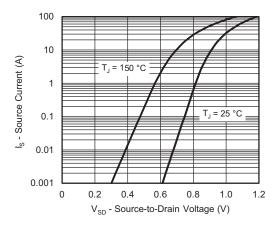
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



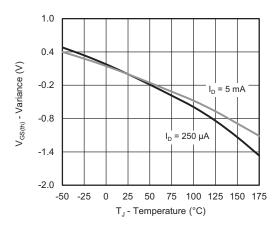
On-Resistance vs. Junction Temperature



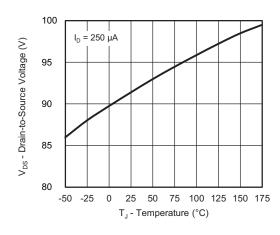
On-Resistance vs. Gate-to-Source Voltage



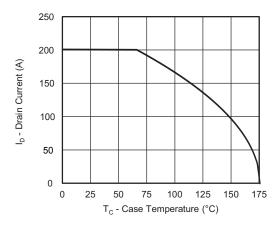
Source Drain Diode Forward Voltage



Threshold Voltage



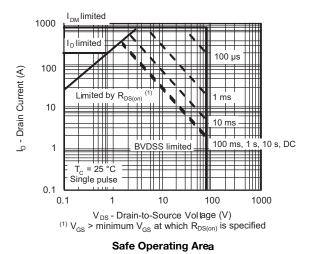
Drain Source Breakdown vs. Junction Temperature

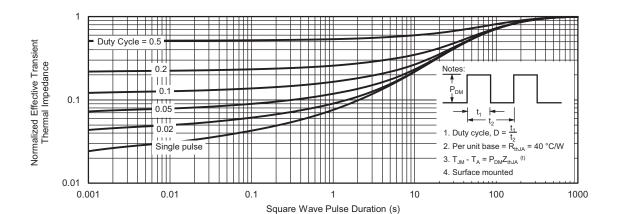


Current De-Rating



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

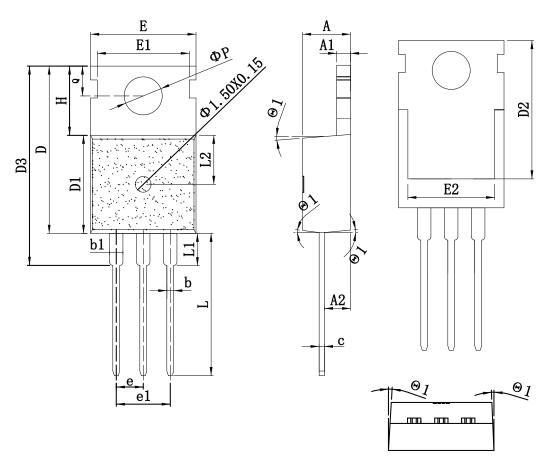




Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-220_3L-A PACKAGE OUTLINE

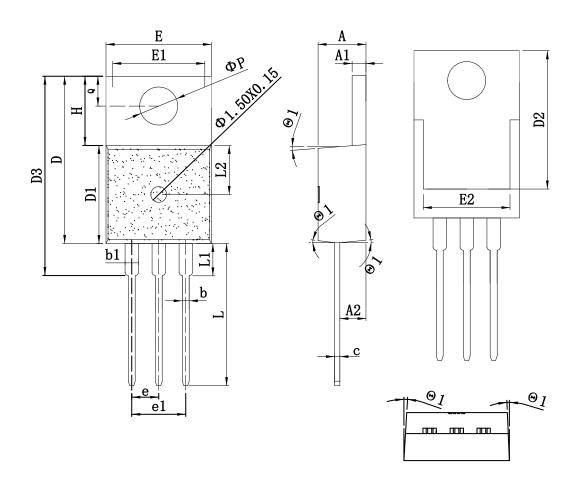


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| SYMBOL | mm | | | SYMBOL | mm | | |
|--------|-------|-------|-------|--------|---------|-------|-------|
| SIMBOL | MIN | TYP | MAX | SIMBOL | MIN | TYP | MAX |
| A | 4.15 | 4.50 | 4.80 | E1 | 8.25 | 8.70 | 9.15 |
| A1 | 1.15 | 1.30 | 1.50 | E2 | 7.20 | 8.00 | 8.80 |
| A2 | 2.10 | 2.40 | 2.65 | e | 2.38 | 2.54 | 2.74 |
| ь | 0.65 | 0.80 | 1.00 | e1 | 5.08REF | | |
| b1 | 1.10 | 1.33 | 1.80 | Н | 6.20 | 6.50 | 6.90 |
| С | 0.35 | 0.50 | 0.65 | L | 12.75 | 13.28 | 13.70 |
| D | 14.25 | 15.75 | 16.15 | L1 | - | 1 | 3.50 |
| D1 | 8.70 | 9.20 | 9.60 | L2 | 2.30 | 4.65 | 7.00 |
| D2 | 12.30 | 13.10 | 13.85 | φP | 3.40 | 3.65 | 3.85 |
| D3 | 16.20 | 18.80 | 20.60 | Q | 2.50 | 2.80 | 3.00 |
| Е | 8.68 | 10.02 | 11.00 | θ | 2° | - | 7° |



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | mm | | | SYMBOL | mm | | |
|--------|-------|-------|-------|--------|-------|---------|-------|
| SIMBOL | MIN | TYP | MAX | SIMBOL | MIN | TYP | MAX |
| A | 4.15 | 4.50 | 4.80 | E1 | 8.25 | 8.70 | 9.15 |
| A1 | 1.15 | 1.30 | 1.50 | E2 | 7.20 | 8.00 | 8.80 |
| A2 | 2.10 | 2.40 | 2.65 | e | 2.38 | 2.54 | 2.74 |
| ь | 0.65 | 0.80 | 1.00 | e1 | | 5.08REF | |
| b1 | 1.10 | 1.33 | 1.80 | Н | 6.20 | 6.50 | 6.90 |
| c | 0.35 | 0.50 | 0.65 | L | 12.75 | 13.28 | 13.70 |
| D | 14.25 | 15.75 | 16.15 | L1 | - | - | 3.50 |
| D1 | 8.70 | 9.20 | 9.60 | L2 | 2.30 | 4.65 | 7.00 |
| D2 | 12.30 | 13.10 | 13.85 | φP | 3.40 | 3.65 | 3.85 |
| D3 | 16.20 | 18.80 | 20.60 | Q | 2.50 | 2.80 | 3.00 |
| Е | 8.68 | 10.02 | 11.00 | θ | 2° | - | 7° |





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